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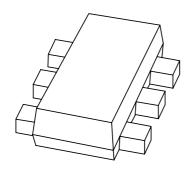
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

# DISCRETE SEMICONDUCTORS

# DATA SHEET



# **BAT960**Schottky barrier diode

Product data sheet Supersedes data of 2002 Jun 24 2003 May 01



# Schottky barrier diode

**BAT960** 

#### **FEATURES**

- · High current capability
- · Very low forward voltage
- Ultra small plastic SMD package
- Flat leads: excellent coplanarity and improved thermal behaviour.

#### **APPLICATIONS**

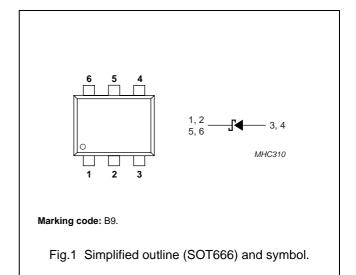
- · Ultra high-speed switching
- · rectification
- DC/DC conversion
- Switch mode power supply
- Inverse polarity protection.

#### **GENERAL DESCRIPTION**

Planar Schottky barrier diode with an integrated guard ring for stress protection in a SOT666 ultra small SMD plastic package.

#### **PINNING**

PIN	DESCRIPTION	
1	cathode	
2	cathode	
3	anode	
4	anode	
5	cathode	
6	cathode	



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>R</sub>	continuous reverse voltage		_	23	V
IF	continuous forward current		_	1	А
I <sub>FSM</sub>	non-repetitive peak forward current	t = 8.3 ms half sinewave; JEDEC method; note 1	_	8	А
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T <sub>amb</sub>	operating ambient temperature		-65	+125	°C

#### Note

1. Only valid, if pins 3 and 4 are connected in parallel.

# Schottky barrier diode

**BAT960** 

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	405	K/W
		note 2	215	K/W

#### **Notes**

- 1. Refer to SOT666 standard mounting conditions.
- 2. Mounted on printed circuit-board, 1  ${\rm cm}^2$  copper area.

#### Soldering

The only recommended soldering method is reflow soldering.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V <sub>F</sub>	continuous forward voltage	I <sub>F</sub> = 10 mA	240	270	mV
		I <sub>F</sub> = 100 mA	300	350	mV
		I <sub>F</sub> = 1000 mA; note 1; see Fig.2	480	550	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 5 V; note 2	5	10	μΑ
		V <sub>R</sub> = 8 V; note 2	7	20	μΑ
		V <sub>R</sub> = 15 V; note 2; see Fig.3	10	50	μΑ
C <sub>d</sub>	diode capacitance	$V_R = 5 \text{ V}$ ; $f = 1 \text{ MHz}$ ; see Fig.4	19	25	pF

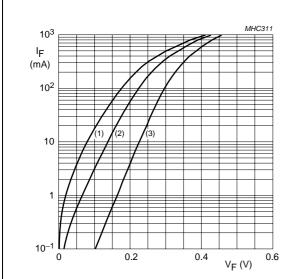
#### **Notes**

- 1. Only valid, if pins 1, 2, 5 and 6 are soldered on a 1 cm<sup>2</sup> copper solder land.
- 2. Pulse test:  $t_p$  = 300  $\mu$ s;  $\delta$  = 0.02.

# Schottky barrier diode

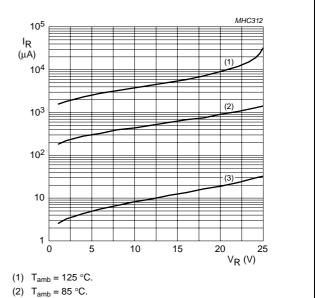
**BAT960** 

#### **GRAPHICAL DATA**



- (1) T<sub>amb</sub> = 125 °C.
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.2 Forward current as a function of forward voltage; typical values.



- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.3 Reverse current as a function of reverse voltage; typical values.

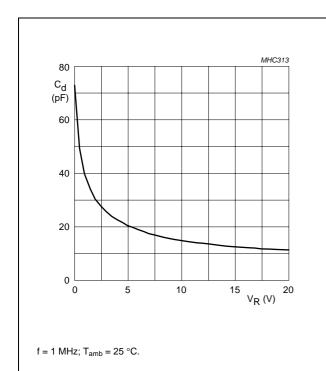


Fig.4 Diode capacitance as a function of reverse voltage; typical values.

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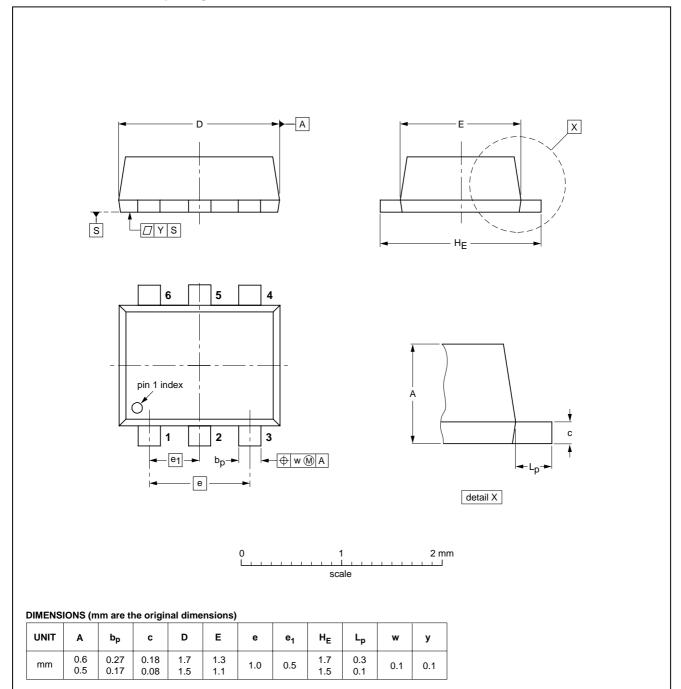
# Schottky barrier diode

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#### **PACKAGE OUTLINE**

Plastic surface mounted package; 6 leads

SOT666



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE DA	
SOT666						<del>-01-01-04</del> 01-08-27

### Schottky barrier diode

**BAT960** 

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### **Notes**

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published
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## **NXP Semiconductors**

#### **Customer notification**

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#### **Contact information**

For additional information please visit: http://www.nxp.com

For sales offices addresses send e-mail to: salesaddresses@nxp.com

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